

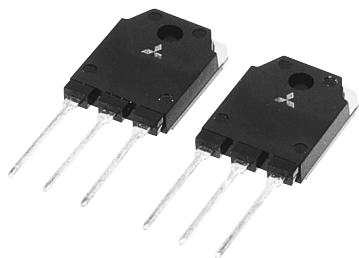
PRELIMINARY
 Notice: This is not a final specification.
 Some parametric limits are subject to change.

MITSUBISHI Pch POWER MOSFET

FX30SMJ-3

HIGH-SPEED SWITCHING USE

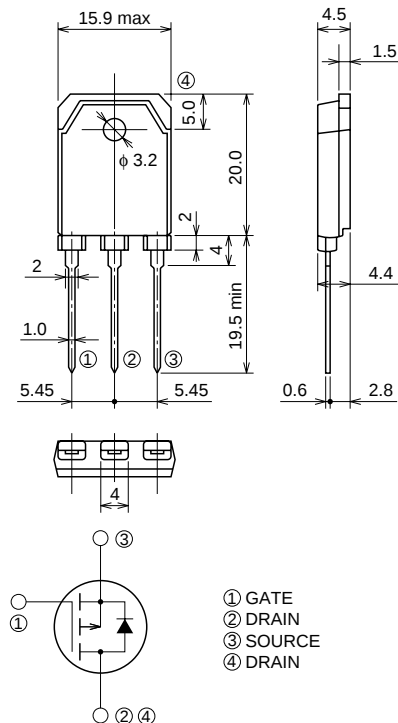
FX30SMJ-3



- 4V DRIVE
- V_{DS} -150V
- $r_{DS(ON)}$ (MAX) $100m\Omega$
- I_D -30A
- Integrated Fast Recovery Diode (TYP.) 100ns

OUTLINE DRAWING

Dimensions in mm



T0-3P

APPLICATION

Motor control, Lamp control, Solenoid control
 DC-DC converter, etc.

MAXIMUM RATINGS (Tc = 25°C)

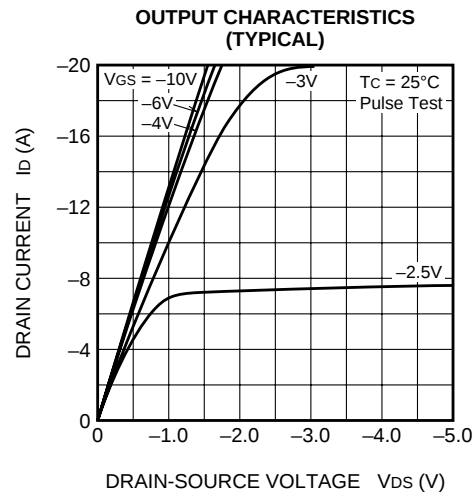
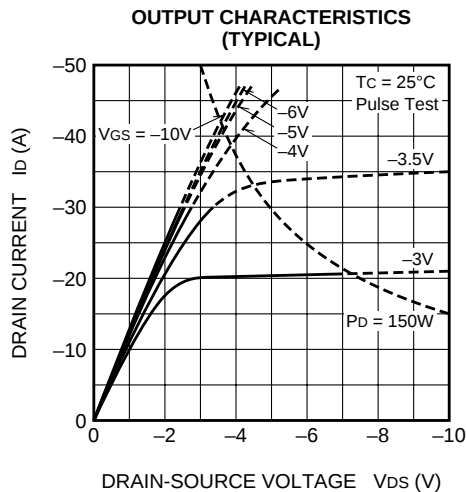
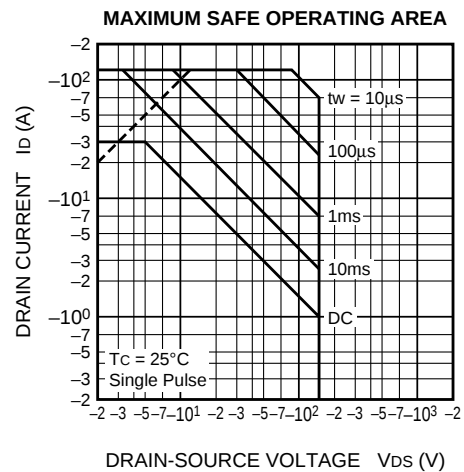
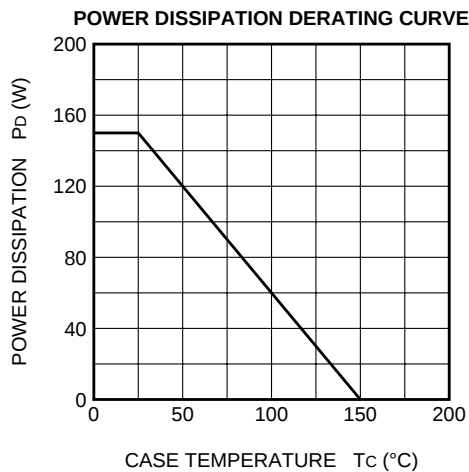
Symbol	Parameter	Conditions	Ratings	Unit
V_{DS}	Drain-source voltage	$V_{GS} = 0V$	-150	V
V_{GSS}	Gate-source voltage	$V_{DS} = 0V$	± 20	V
I_D	Drain current		-30	A
I_{DM}	Drain current (Pulsed)		-120	A
I_{DA}	Avalanche drain current (Pulsed)	$L = 30\mu H$	-30	A
I_S	Source current		-30	A
I_{SM}	Source current (Pulsed)		-120	A
P_D	Maximum power dissipation		150	W
T_{ch}	Channel temperature		-55 ~ +150	°C
T_{stg}	Storage temperature		-55 ~ +150	°C
—	Weight	Typical value	4.8	g

Jan.1999

ELECTRICAL CHARACTERISTICS (Tch = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V(BR)DSS	Drain-source breakdown voltage	Id = -1mA, Vgs = 0V	-150	—	—	V
IGSS	Gate-source leakage current	Vgs = ±20V, Vds = 0V	—	—	±0.1	μA
IDSS	Drain-source leakage current	Vds = -150V, Vgs = 0V	—	—	-0.1	mA
VGS(th)	Gate-source threshold voltage	Id = -1mA, Vds = -10V	-1.0	-1.5	-2.0	V
rDS(ON)	Drain-source on-state resistance	Id = -15A, Vgs = -10V	—	78	100	mΩ
rDS(ON)	Drain-source on-state resistance	Id = -15A, Vgs = -4V	—	85	111	mΩ
VDS(ON)	Drain-source on-state voltage	Id = -15A, Vgs = -10V	—	-1.17	-1.50	V
yfs	Forward transfer admittance	Id = -15A, Vds = -10V	—	41.3	—	S
Ciss	Input capacitance	Vds = -10V, Vgs = 0V, f = 1MHz	—	11430	—	pF
Coss	Output capacitance		—	674	—	pF
Crss	Reverse transfer capacitance		—	320	—	pF
td(on)	Turn-on delay time	VDD = -80V, Id = -15A, Vgs = -10V, RGEN = RGS = 50Ω	—	61	—	ns
tr	Rise time		—	99	—	ns
td(off)	Turn-off delay time		—	878	—	ns
tf	Fall time		—	330	—	ns
VSD	Source-drain voltage	Is = -15A, Vgs = 0V	—	-1.0	-1.5	V
Rth(ch-c)	Thermal resistance	Channel to case	—	—	0.83	°C/W
trr	Reverse recovery time	Is = -30A, dis/dt = 100A/μs	—	100	—	ns

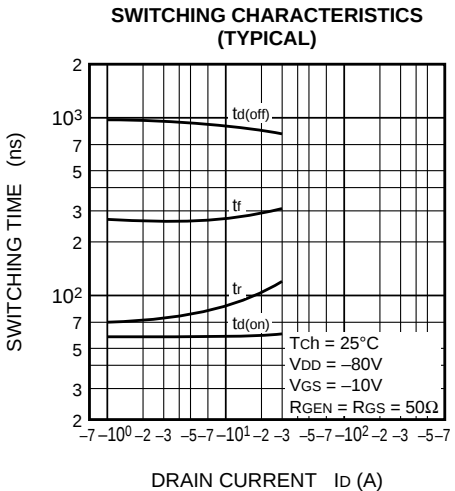
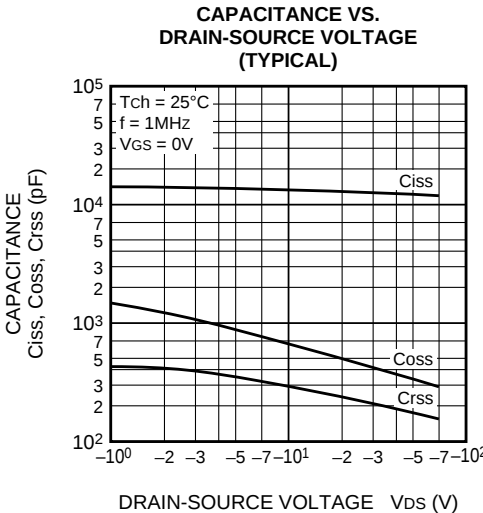
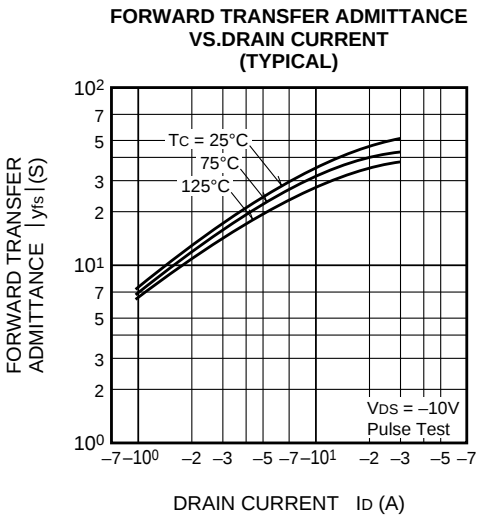
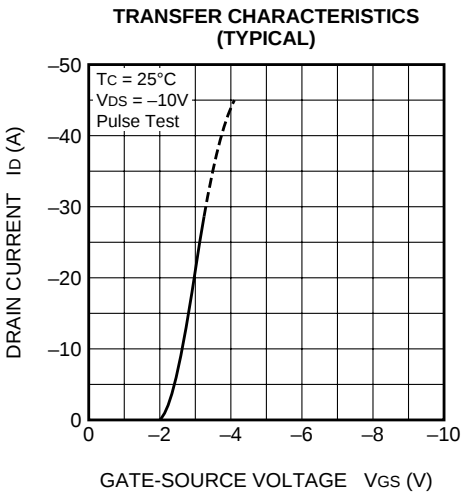
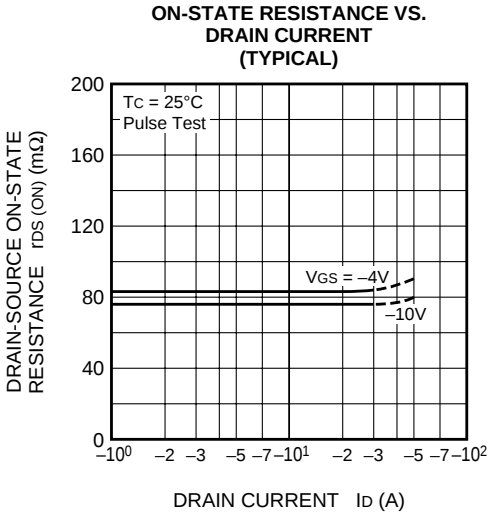
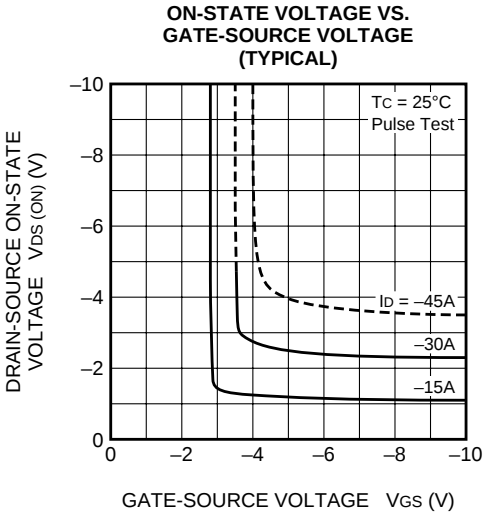
PERFORMANCE CURVES



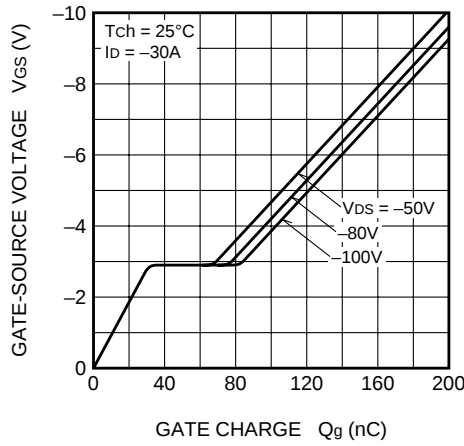
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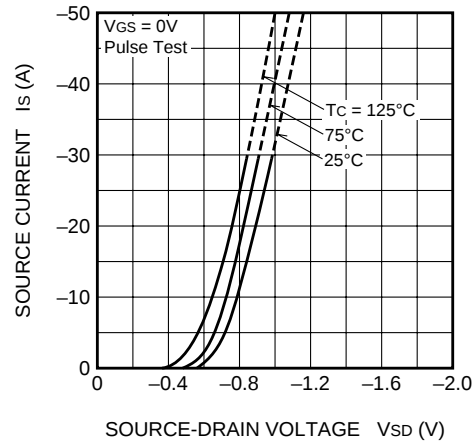
HIGH-SPEED SWITCHING USE



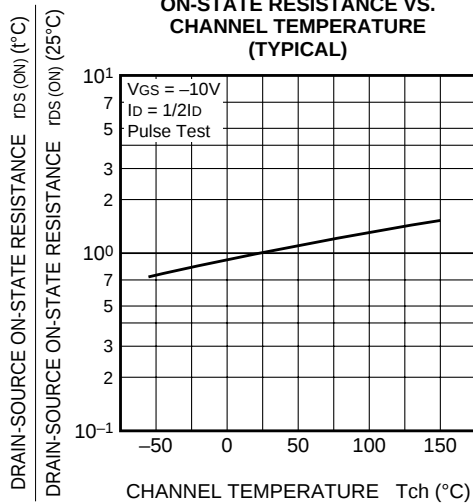
**GATE-SOURCE VOLTAGE
 VS. GATE CHARGE
 (TYPICAL)**



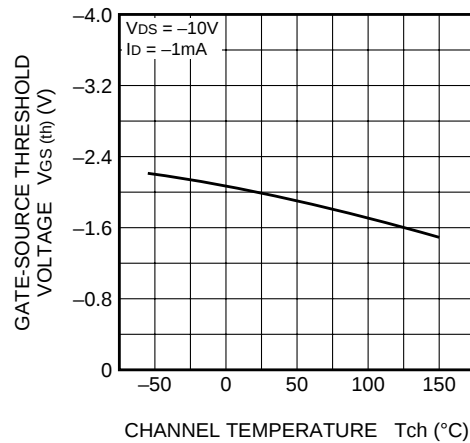
**SOURCE-DRAIN DIODE
 FORWARD CHARACTERISTICS
 (TYPICAL)**



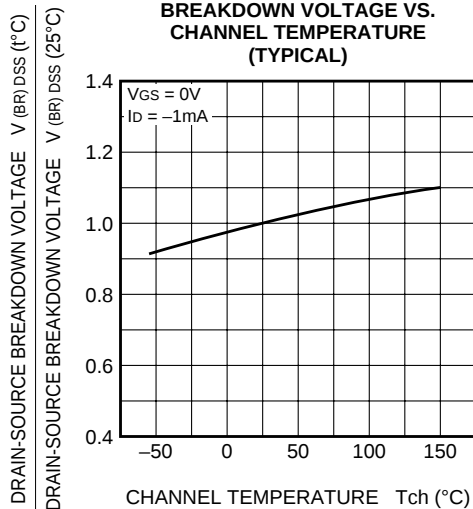
**ON-STATE RESISTANCE VS.
 CHANNEL TEMPERATURE
 (TYPICAL)**



**THRESHOLD VOLTAGE VS.
 CHANNEL TEMPERATURE
 (TYPICAL)**



**BREAKDOWN VOLTAGE VS.
 CHANNEL TEMPERATURE
 (TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE
 CHARACTERISTICS**

